

60 V, 5 A PNP low V_{CEsat} (BISS) transistor Rev. 01 — 1 April 2010

Product data sheet

Product profile 1.

1.1 General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power and flat lead SOT89 (SC-62) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4041NX.

1.2 Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- AEC-Q101 qualified
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
l _C	collector current		-	-	-5	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$	-	-	-15	A
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = -4 \text{ A};$ $I_{B} = -400 \text{ mA}$	<u>[1]</u> _	40	60	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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Pinning information 2.

Table 2.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	emitter		_
2	collector		2
3	base		3
			006aaa231

Ordering information 3.

Table 3. Orde	ering inform	nation	
Type number	Package		
	Name	Description	Version
PBSS4041PX	SC-62	plastic surface-mounted package; 3 leads	SOT89

Marking 4.

Table 4. Marking codes	;
Type number	Marking code ^[1]
PBSS4041PX	*6G
PBSS4041PX	*6G

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

Limiting values 5.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	-	-60	V
V _{CEO}	collector-emitter voltage	open base	-	-60	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
l _C	collector current		-	-5	А
I _{CM}	peak collector current	single pulse; $t_p \leq 1 ms$	-	-15	A
I _B	base current		-	-1	А

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Table 5.	Limiting	values	continued
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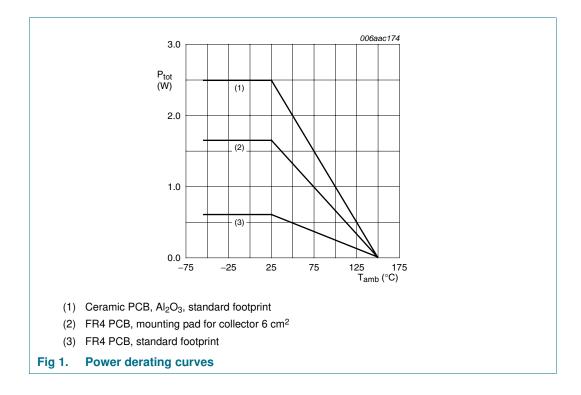
In accordance with the Absolute Maximum Rating System (IEC 60134).

			,		
Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} \leq 25 \ ^{\circ}C$	[1] -	600	mW
			[2] -	1650	mW
			[3] _	2500	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.



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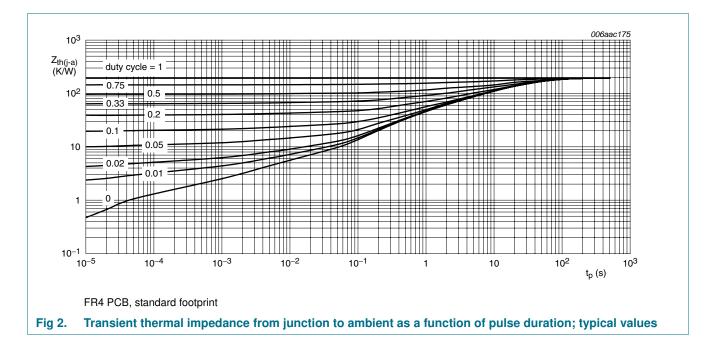
6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	210	K/W
			[2] _	-	75	K/W
			<u>[3]</u> _	-	50	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

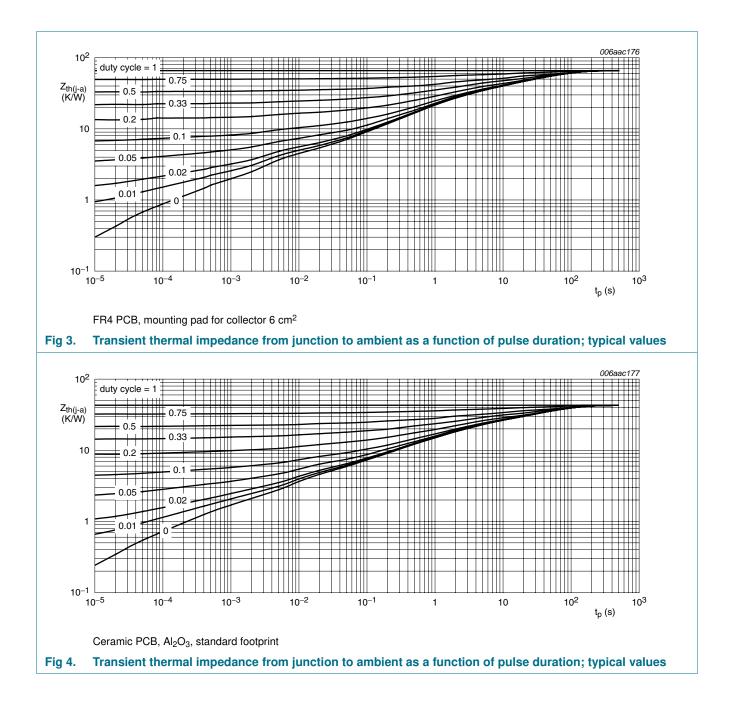
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.



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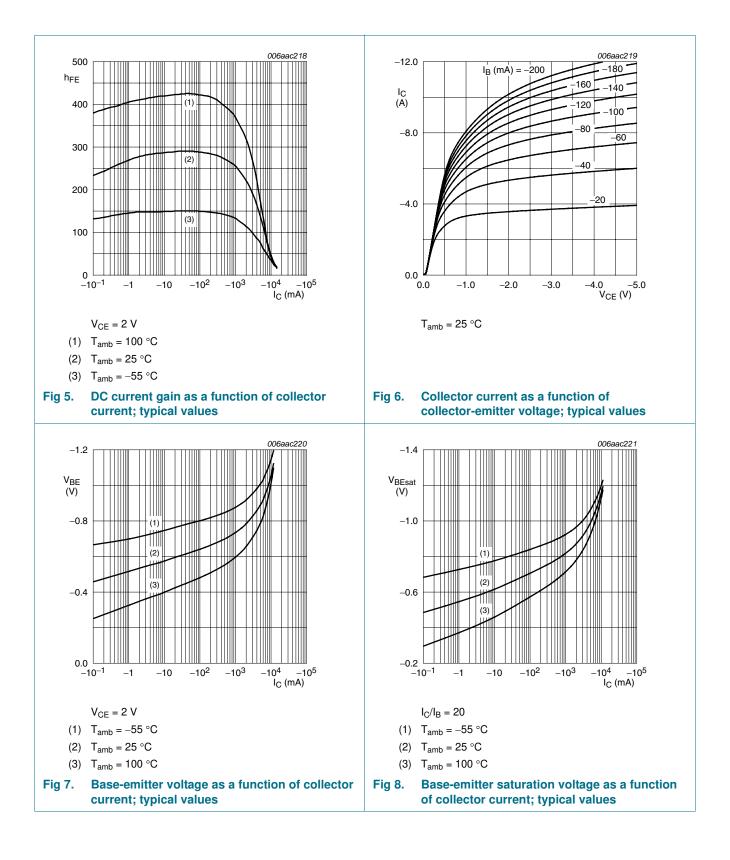
7. Characteristics

Table 7. T _{amb} = 25	Characteristics	pecified.					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}		$V_{CB} = -60 \text{ V}; \text{ I}_{E} = 0 \text{ A}$		-	-	-100	nA
	current	$\label{eq:VCB} \begin{array}{l} V_{CB} = -60 \ V; \ I_E = 0 \ A; \\ T_j = 150 \ ^\circ C \end{array}$		-	-	-50	μA
I _{CES}	collector-emitter cut-off current	$V_{CE} = -48 \text{ V}; \text{V}_{BE} = 0 \text{ V}$		-	-	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 V$	[1]				
		I _C = -500 mA		200	300	-	
		$I_{\rm C} = -1$ A		180	270	-	
		$I_{\rm C} = -2$ A		150	250	-	
		$I_{\rm C} = -4$ A		120	180	-	
		$I_{\rm C} = -6 {\rm A}$		80	125	-	
V _{CEsat}	collector-emitter		[1]				
:	saturation voltage	$I_{C} = -1$ A; $I_{B} = -50$ mA		-	-60	-90	mV
		$I_{C} = -1 \text{ A}; I_{B} = -10 \text{ mA}$		-	-120	-180	mV
		$I_{C} = -2 \text{ A}; I_{B} = -40 \text{ mA}$		-	-145	-210	mV
		$I_{C} = -4 \text{ A}; I_{B} = -200 \text{ mA}$		-	-195	-300	mV
		$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$		-	-160	-240	mV
		$I_{C} = -5 \text{ A}; I_{B} = -500 \text{ mA}$		-	-200	-300	mV
R _{CEsat}	collector-emitter saturation resistance	$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$	[1]	-	40	60	mΩ
V _{BEsat}	base-emitter	$I_{C} = -1 \text{ A}; I_{B} = -100 \text{ mA}$	[1]	-	-0.84	-0.9	V
	saturation voltage	$I_{C} = -4 \text{ A}; I_{B} = -400 \text{ mA}$	[1]	-	-0.98	-1.05	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V}; \text{ I}_{C} = -2 \text{ A}$	<u>[1]</u>	-	-0.77	-0.85	V
t _d	delay time	$V_{CC} = -12.5 V;$		-	45	-	ns
t _r	rise time	$I_{\rm C} = -1 \text{ A}; I_{\rm Bon} = -0.05 \text{ A};$		-	60	-	ns
t _{on}	turn-on time	$I_{Boff} = 0.05 \text{ A}$		-	105	-	ns
ts	storage time			-	440	-	ns
t _f	fall time			-	75	-	ns
t _{off}	turn-off time			-	515	-	ns
f _T	transition frequency	$V_{CE} = -10 \text{ V};$ $I_{C} = -100 \text{ mA};$ f = 100 MHz		-	110	-	MHz
C _c	collector capacitance	$\label{eq:VCB} \begin{array}{l} V_{CB} = -10 \ V; \\ I_E = i_e = 0 \ A; \ f = 1 \ MHz \end{array}$		-	85	-	pF

 $\label{eq:point} \begin{tabular}{ll} \begin{$

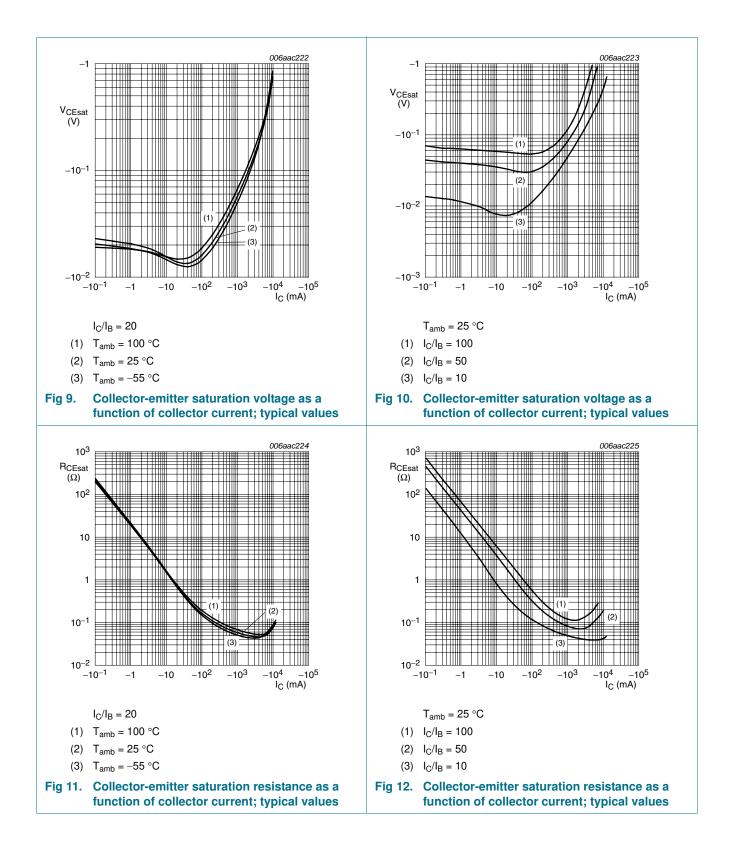
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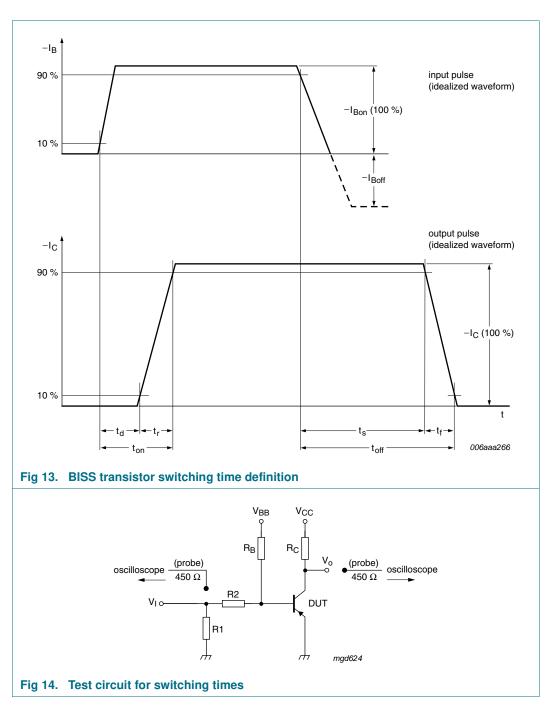
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8. Test information

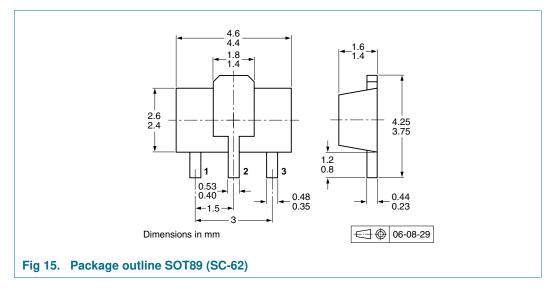


8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	e number Package Description			Packing quantity	
				3000	10000
PBSS4041PX SOT89	8 mm pitch, 12 mm tape and reel; T1	[2]	-115	-135	
		8 mm pitch, 12 mm tape and reel; T3	[3]	-120	-

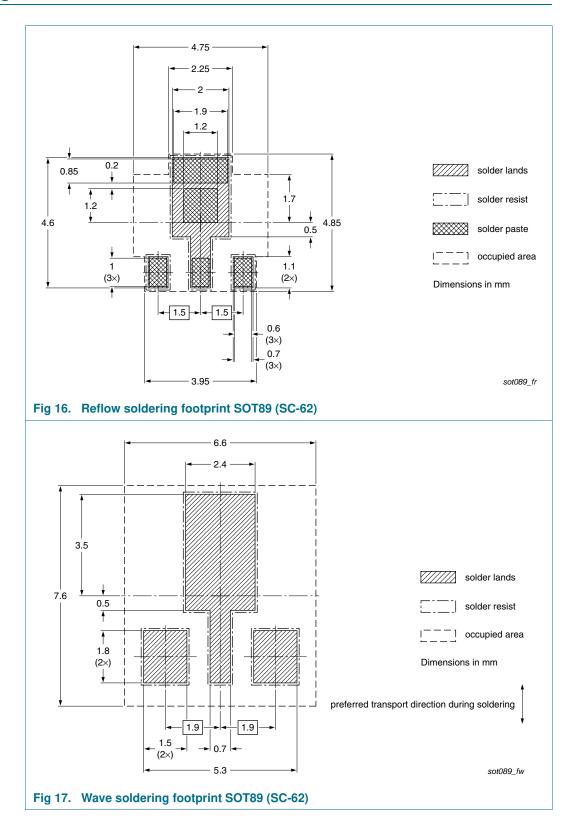
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

[2] T1: normal taping

[3] T3: 90° rotated taping

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11. Soldering



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12. Revision history

Table 9.Revision his	tory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4041PX_1	20100401	Product data sheet	-	-

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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14. Contact information

For more information, please visit: http://www.nexperia.com

For sales office addresses, please send an email to: salesaddresses@nexperia.com

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